

Form PTO-1449

US DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 1 of 1

Complete if Known

Application Number	09/997,997
Filing Date	November 30, 2001
First Named Inventor	Tomohiko SHIBATA
Art Unit	2834
Examiner Name	Not Assigned
Confirmation No.	3908
Attorney Docket No.	782_200

**U.S. PATENT DOCUMENTS**

Exam. Initial	Document Number	Date	Name	Class	Sub Class	Filing Date

**FOREIGN PATENT DOCUMENTS**

Document Number	Date	Country	Class	Sub Class	Translation	Abstract

**OTHER DOCUMENTS**

(Including Author, Title, Date, Pertinent Pages etc.)

AA	S. Kaneko, et al, "Epitaxial Growth of AlN Film by Low-pressure MOCVD in Gas-Beam-Flow Reactor," Journal of Crystal Growth, 115 (1991), pp. 643-647.

Examiner: <i>AA-guicel</i>	Date Considered: 40/15/03
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.